

FEATURES

■ LOW INTERMODULATION DISTORTION

IM3=-45 dBc at Pout= 31.5dBm
Single Carrier Level

■ HIGH POWER

P1dB=42.5dBm at 5.85GHz to 6.75GHz

■ HIGH GAIN

G1dB=8.0dB(min.) at 5.85GHz to 6.75GHz

■ BROAD BAND INTERNALLY MATCHED FET

■ HERMETICALLY SEALED PACKAGE

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V f= 5.85 to 6.75GHz	dBm	41.5	42.5	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	8.0	—	—
Drain Current	IDS1		A	—	4.4	5.0
Gain Flatness	ΔG		dB	—	—	±0.8
Power Added Efficiency	ηadd		%	—	35	—
3 rd Order Intermodulation Distortion	IM3	Two-Tone Test Po=31.5dBm (Single Carrier Level)	dBc	-42	-45	—
Drain Current	IDS2		A	—	4.4	5.0
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin - P1dB) X Rth(c-c)	°C	—	—	80

Recommended Gate Resistance(Rg): 100 Ω (Max.)

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

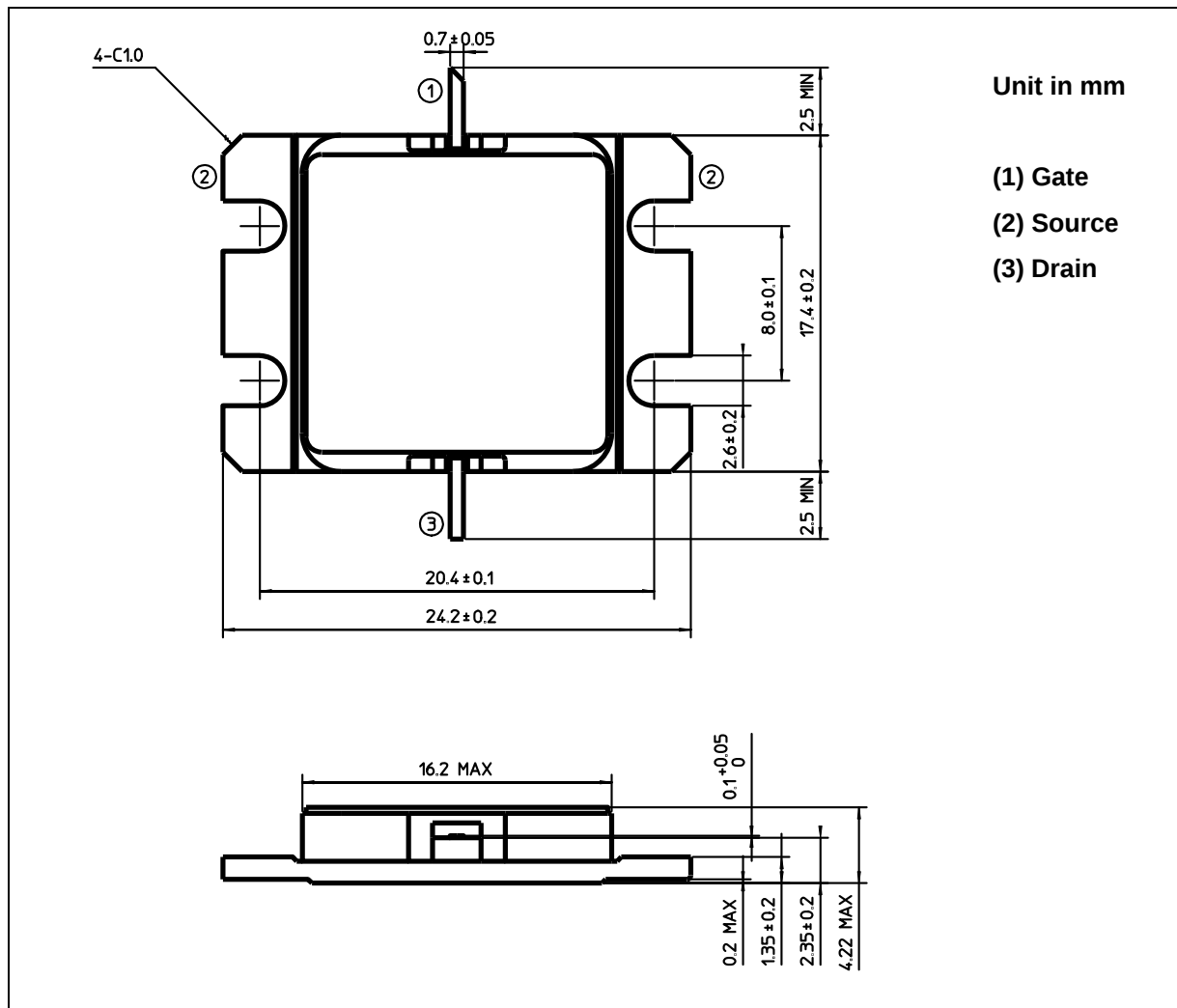
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 6A	mS	—	3600	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 60mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	10.5	—
Gate-Source Breakdown Voltage	VGSO	IGS= -200μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	1.5	2.0

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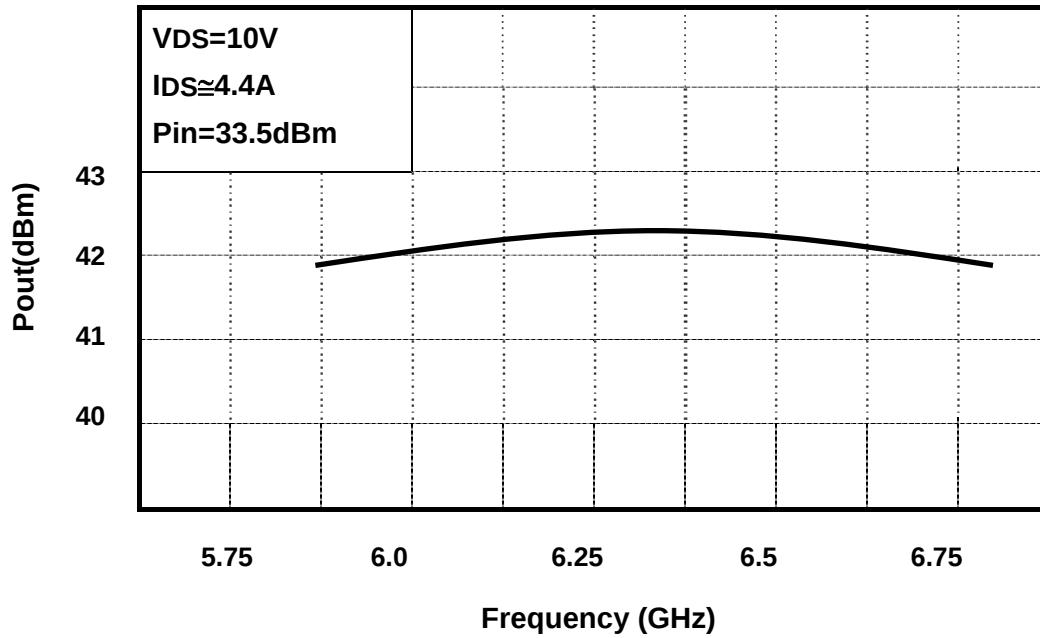
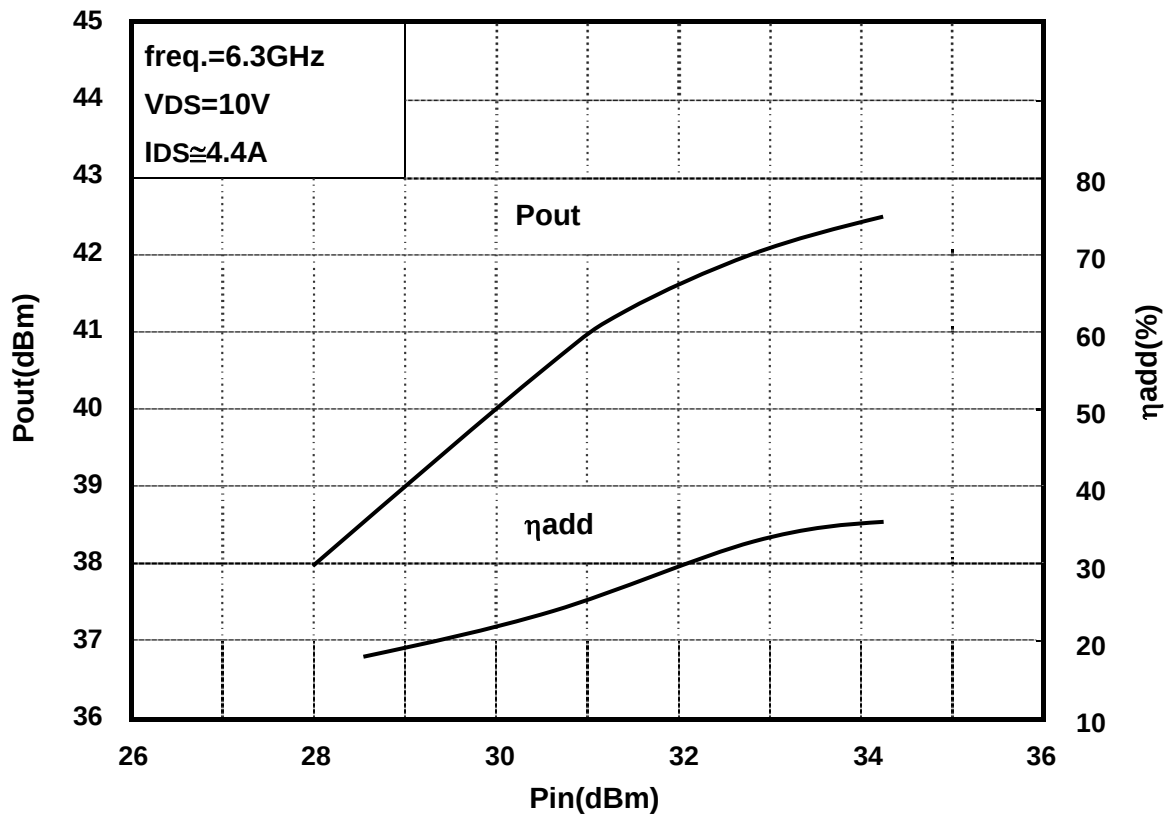
The information contained herein is subject to change without prior notice. It is therefor advisable to contact TOSHIBA before proceeding with design of equipment incorporating this product.

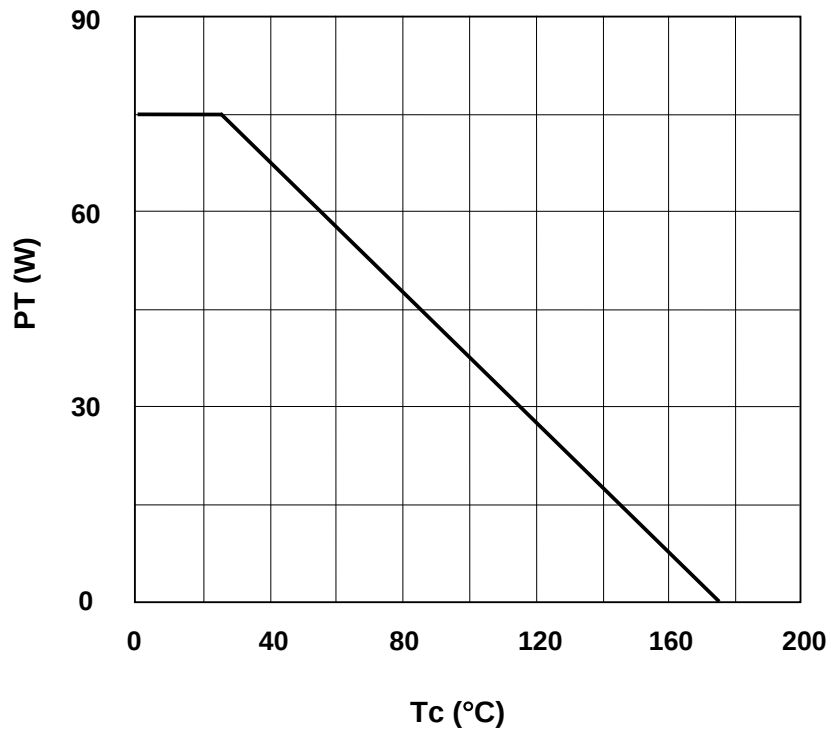
ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	V _{DS}	V	15
Gate-Source Voltage	V _{GS}	V	-5
Drain Current	I _{DS}	A	14.0
Total Power Dissipation (T _c = 25 °C)	P _T	W	75.0
Channel Temperature	T _{ch}	°C	175
Storage Temperature	T _{stg}	°C	-65 to +175

PACKAGE OUTLINE (2-16G1B)**HANDLING PRECAUTIONS FOR PACKAGE MODEL**

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

RF PERFORMANCE**Output Power vs. Frequency****Output Power(Pout) vs. Input Power(Pin)**

Power Dissipation vs. Case Temperature**IM3 vs. Output Power Characteristics**